Element Specific Diagnosis Using $\mu$-PCD

L. Köster, P. Blöchl, L. Fabry
Wacker-Chemitronic GmbH, D-84489 Burghausen, Germany

The photoconductive decay technique, using the change of reflectivity of microwaves after pulsed optical excitation of excess minority carriers, is a very convenient, i.e. nondestructive, contactless and fast way for the indirect in-line monitoring of metallic contamination in silicon [1, 2]. Although the phenomenon of $\mu$-PCD was known for decades [3], recently, it has attracted high interest due to the availability of automated and computerized equipment with both high lifetime resolution (0.1 $\mu$s) in a range of 0.1 $\mu$s-10 $\mu$s and lateral resolution (1 mm) [4].

For certain metals, the recombination lifetime, per se, is not specifically sensitive. The contamination level due to lifetime data, however, can be understood by a simple correlation equation that has been established for the concentration of Fe (C) as a monitor element in B-doped CZ-Si [5]:

$$\tau(\mu s) = 10^{13}/C_{\text{Fe(atoms/cm}^3)}$$

Eq. 1

Thus, a concentration of $10^{12}$ Fe at.cm$^{-3}$ already limits the lifetime to 10 $\mu$s. The detection limit for metals is estimated to be about $10^{10}$ at.cm$^{-3}$. Similar results were found for Ti in specially grown B-doped CZ-crystals of Si (Fig. 1).

Three aspects must be taken into account when tracking down metallic contamination:
1. The diffusion coefficient of the element of interest in monocrystalline silicon
2. Its solubility and saturation concentration in monocrystalline silicon at the drive-in / diffusion temperature
3. Distribution of the lifetime killer between electrically active and inactive sites including solid state chemical reactions

Lifetime and DLTS data on B-doped FZ wafers confirmed the anticipation after different thermal processes in a contaminated annealing furnace (Fig. 2).

In order to estimate the influence of one Fe particle of the size of 0.3 $\mu$m we can calculate from Eq. 1 that it can locally reduce the lifetime to less than 100 $\mu$s after drive-in at high temperature. Alkaline cleaning solutions containing 50 pptrw Fe are in equilibrium with the same amount of Fe (1x10$^{10}$ at.cm$^{-3}$). Due to known adsorption isotherms [6], 10 pptrw Fe corresponds only to 1/5 of the above surface contamination. However, the lifetime would increase to 1000 $\mu$s after drive-in.

If absolute lifetime values are required, the measured effective lifetime can be traced back to the thickness of a wafer if both high surface recombination rate and low bulk recombination rate are provided (Fig. 3).

Unfortunately, the integrative parameter "lifetime" is influenced by many other elements or defects such as Pt or Au, by crystal defects, oxygen precipitates and even contaminants can interfere with each other. The injection level also affects the effective carrier lifetime [7]. As yet, much work has to be done in order to recognize, identify, understand and separate these influences.

REFERENCES


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### Table 1.

Diffusion length after 10 min. of diffusion and the solubility of Fe, Cu and Ni in monocrystalline silicon

<table>
<thead>
<tr>
<th>Temperature (°C)</th>
<th>Fe</th>
<th>Cu</th>
<th>Ni</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td>L</td>
<td>S</td>
<td>L</td>
</tr>
<tr>
<td>600</td>
<td>30.4</td>
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</tr>
<tr>
<td>800</td>
<td>70.7</td>
<td>10²</td>
<td>2.000</td>
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<tr>
<td>1.000</td>
<td>126</td>
<td>10⁴</td>
<td>2.760</td>
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<tr>
<td>1.100</td>
<td>158</td>
<td>10⁵</td>
<td>3.160</td>
</tr>
<tr>
<td>1.200</td>
<td>192</td>
<td>10⁶</td>
<td>3.560</td>
</tr>
</tbody>
</table>

Table 2.

µ-PCD lifetimes and DLTS trap concentrations of p-type FZ Si after various thermal treatments in a contaminated annealing furnace.

#### Figure 1

SPV- and µ-PCD-lifetimes of Ti-doped p-type CZ-Si.

Ti concentration determined by DLTS.

#### Figure 2

DLTS-spectra of p-type FZ after various thermal treatments in a contaminated annealing furnace.

#### Figure 3

Measured effective lifetimes on lapped wafers of various thicknesses.

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